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#15 pre.ama 12/11/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: KANO et al.

Group Art Unit: 2812

Serial No.: 09/941,982

Examiner: Mulpuri, Savitri

Filed: August 30, 2001

P.T.O. Confirmation No.: 7536

For.

METHOD OF FORMING NITRIDE-BASED SEMICONDUCTOR LAYER, AND METHOD OF MANUFACTURING NITRIDE-BASED SEMICONDUCTOR

DEVICE

PRELIMINARY AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Date: October 9, 2003

Sir:

Prior to continued examination, please amend the above-identified application as follows:

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OCT 1 5 2003

TECHNOLOGY CENTER 2860

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Docket No.: 011083

Filed: August 30, 2001

OCT 0 8 2003 Issued:

Papers filed herewith on: 10/09/03

Applicant(s): KANO et al.

Patent Number:

U.S. Patent Application Serial No.: 09/941,982 Fee: \$1,190.00 RCE; 2 month EOT; Preliminary Amendment and Change

Receipt is hereby acknowledged of the papers filed as indicated in connection with the above-identified COMMISSIONER OF PATENTS

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